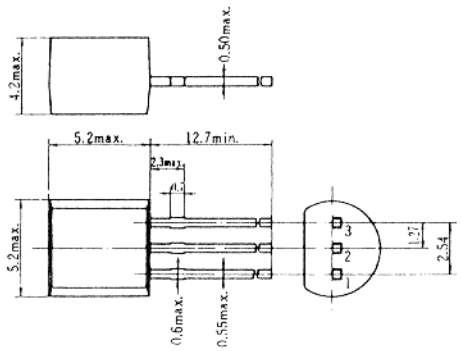
HITACHI

查询"2SB1348"供应商

2SB1348, 2SB1349

SILICON PNP EPITAXIAL

LOW FREQUENCY HIGH VOLTAGE AMPLIFIER



1. Emitter
2. Collector
3. Base

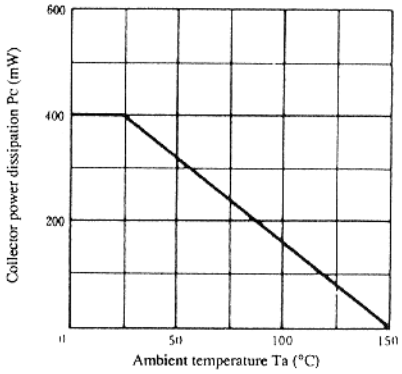
(Dimensions in mm)

(JEDEC TO-92)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB1348	2SB1349	Unit
Collector to base voltage	V_{CBO}	−160	−200	V
Collector to emitter voltage	V_{CEO}	−160	−200	V
Emitter to base voltage	V_{EBO}	−5	−5	V
Collector current	I_C	−100	−100	mA
Collector power dissipation	P_C	400	400	mW
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	−55 to +150	−55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

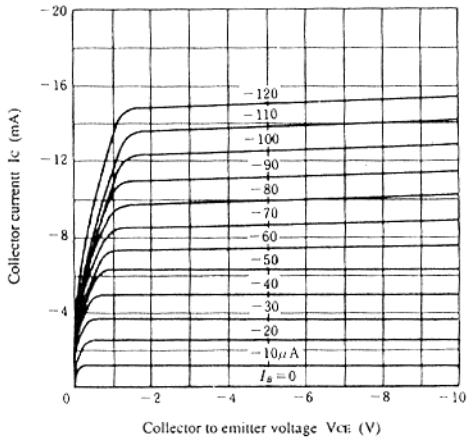
Item	Symbol	Test Condition		min.	typ.	max.	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	I_C = −10μA, I_E = 0	2SB1348	−160	—	—	V
			2SB1349	−200	—	—	V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	I_C = −1mA, R_{BE} = ∞	2SB1348	−160	—	—	V
			2SB1349	−200	—	—	V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	I_E = −10μA, I_C = 0		−5	—	—	V
Collector cutoff current	I_{CBO}	2SB1348	V_{CB} = −140V, I_E = 0	—	—	−10	μA
		2SB1349	V_{CB} = −160V, I_E = 0	—	—	−10	μA
DC current transfer ratio	h_{FE1}*	V_{CE} = −5V, I_C = −10mA		60	—	200	
	h_{FE2}	V_{CE} = −5V, I_C = −1mA		30	—	—	
Base to emitter voltage	V_{BE}	V_{CE} = −5V, I_C = −10mA		—	—	−1.5	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = −30mA, I_B = −3mA		—	—	−0.5	V
Gain bandwidth product	f_T	V_{CE} = −5V, I_C = −10mA		—	140	—	MHz
Collector output capacitance	C_{ob}	V_{CB} = −10V, I_E = 0, f = 1MHz		—	5.5	—	pF

* The 2SB1348 and 2SB1349 are grouped by h_{FE1} as follows.

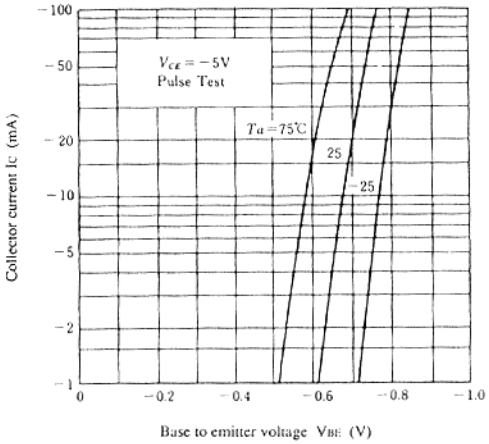
Grade	B	C
h_{FE1}	60 to 120	100 to 200

2SB1348, 2SB1349

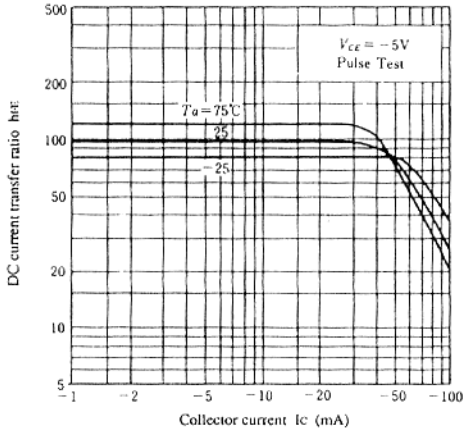
TYPICAL OUTPUT CHARACTERISTICS



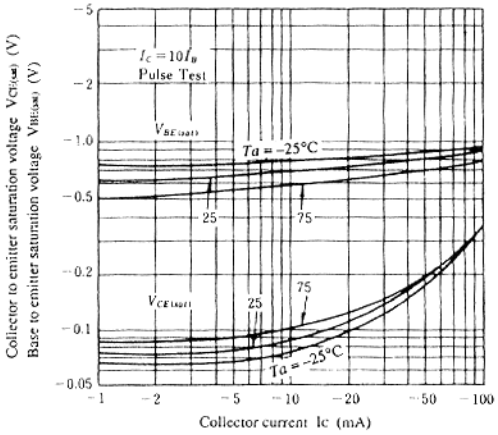
TYPICAL TRANSFER CHARACTERISTICS



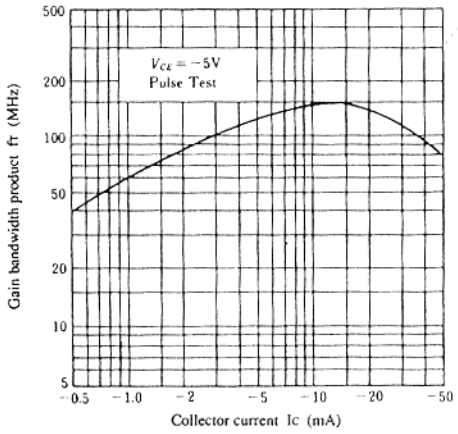
DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



SATURATION VOLTAGE VS. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT VS. COLLECTOR CURRENT



COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE